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a thin film transistor connected to one of the data lines and one of the gate lines defining the cell,
a storage capacitor, and
a metallic pattern, surrounding the cell, including a drain electrode of the thin film transistor and a storage electrode of the storage capacitor in a single layer and being electrically connected to the pixel electrode, wherein the storage electrode is formed over the one of the gate lines.

21. (Three Times Amended) A liquid crystal device having a thin film transistor, comprising:

a plurality of gate lines formed on a substrate;
a plurality of data lines insulated from and intersecting said gate lines, said data lines and intersecting gate lines defining a plurality of cells, at least one cell including,

a pixel electrode,
a thin film transistor interposed between one of the data lines and the pixel electrode and including a source electrode connected to the one of the data lines, a gate electrode connected to one of the gate lines, a drain electrode, and
a storage capacitor, surrounding the cell, including a storage electrode and a drain electrode in a single layer, the storage capacitor being connected to

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the pixel electrode, wherein the storage electrode is formed over the one of the gate lines.

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23. (Three Times Amended) A method of manufacturing a thin film transistor substrate, comprising:

- forming a gate line having a gate electrode on a transparent substrate;
 - forming a gate insulating layer on the gate electrode;
 - forming a semiconductor layer on the gate insulating layer;
 - simultaneously forming a data line having a source electrode, and a metallic pattern including a drain electrode part and a storage electrode part in a single layer, wherein the storage electrode part is formed over the gate line;
 - forming a protective film over the entire surface; and
 - forming a pixel electrode over the protective film.
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